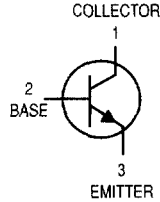


Amplifier Transistors
NPN Silicon

BC182,A,B
BC183
BC184



MAXIMUM RATINGS

Rating	Symbol	BC182	BC183	BC184	Unit
Collector–Emitter Voltage	V_{CEO}	50	30	30	Vdc
Collector–Base Voltage	V_{CBO}	60	45	45	Vdc
Emitter–Base Voltage	V_{EBO}	6.0			Vdc
Collector Current — Continuous	I_C	100			mAdc
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	350			mW
		2.8			mW/ $^\circ\text{C}$
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	1.0			Watts
		8.0			mW/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	–55 to +150			$^\circ\text{C}$

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	357	$^\circ\text{C/W}$
Thermal Resistance, Junction to Case	$R_{\theta JC}$	125	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Collector–Emitter Breakdown Voltage ($I_C = 2.0\text{ mA}, I_B = 0$)	BC182 BC183 BC184	$V_{(BR)CEO}$	50 30 30	— — —	— — —	V
Collector–Base Breakdown Voltage ($I_C = 100\ \mu\text{A}, I_E = 0$)	BC182 BC183 BC184	$V_{(BR)CBO}$	60 45 45	— — —	— — —	V
Emitter–Base Breakdown Voltage ($I_E = 100\ \mu\text{A}, I_C = 0$)		$V_{(BR)EBO}$	6.0	—	—	V
Collector Cutoff Current ($V_{CB} = 50\text{ V}, V_{BE} = 0$) ($V_{CB} = 30\text{ V}, V_{BE} = 0$)	BC182 BC183 BC184	I_{CBO}	— — —	0.2 0.2 0.2	15 15 15	nA
Emitter–Base Leakage Current ($V_{EB} = 4.0\text{ V}, I_C = 0$)		I_{EBO}	—	—	15	nA

BC182,A,B BC183 BC184
ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted) (Continued)

Characteristic	Symbol	Min	Typ	Max	Unit
ON CHARACTERISTICS					
DC Current Gain ($I_C = 10\ \mu\text{A}$, $V_{CE} = 5.0\ \text{V}$) ($I_C = 2.0\ \text{mA}$, $V_{CE} = 5.0\ \text{V}$) ($I_C = 100\ \text{mA}$, $V_{CE} = 5.0\ \text{V}$)	BC182	40	—	—	—
	BC183	40	—	—	—
	BC184	100	—	—	—
	BC182	120	—	500	—
	BC183	120	—	800	—
	BC184	250	—	800	—
	BC182	80	—	—	—
	BC183	80	—	—	—
	BC184	130	—	—	—
Collector–Emitter On Voltage ($I_C = 10\ \text{mA}$, $I_B = 0.5\ \text{mA}$) ($I_C = 100\ \text{mA}$, $I_B = 5.0\ \text{mA}$) ⁽¹⁾	$V_{CE(sat)}$	—	0.07 0.2	0.25 0.6	V
Base–Emitter Saturation Voltage ($I_C = 100\ \text{mA}$, $I_B = 5.0\ \text{mA}$) ⁽¹⁾	$V_{BE(sat)}$	—	—	1.2	V
Base–Emitter On Voltage ($I_C = 100\ \mu\text{A}$, $V_{CE} = 5.0\ \text{V}$) ($I_C = 2.0\ \text{mA}$, $V_{CE} = 5.0\ \text{V}$) ($I_C = 100\ \text{mA}$, $V_{CE} = 5.0\ \text{V}$) ⁽¹⁾	$V_{BE(on)}$	— 0.55 —	0.5 0.62 0.83	— 0.7 —	V
DYNAMIC CHARACTERISTICS					
Current–Gain — Bandwidth Product ($I_C = 0.5\ \text{mA}$, $V_{CE} = 3.0\ \text{V}$, $f = 100\ \text{MHz}$) ($I_C = 10\ \text{mA}$, $V_{CE} = 5.0\ \text{V}$, $f = 100\ \text{MHz}$)	BC182	—	100	—	MHz
	BC183	—	120	—	
	BC184	—	140	—	
	BC182	150	200	—	
	BC183	150	240	—	
	BC184	150	280	—	
Common Base Output Capacitance ($V_{CB} = 10\ \text{V}$, $I_C = 0$, $f = 1.0\ \text{MHz}$)	C_{ob}	—	—	5.0	pF
Common Base Input Capacitance ($V_{EB} = 0.5\ \text{V}$, $I_C = 0$, $f = 1.0\ \text{MHz}$)	C_{ib}	—	8.0	—	pF
Small–Signal Current Gain ($I_C = 2.0\ \text{mA}$, $V_{CE} = 5.0\ \text{V}$, $f = 1.0\ \text{kHz}$)	BC182	125	—	500	—
	BC183	125	—	900	
	BC184	240	—	900	
	BC182A	125	—	260	
	BC182B	240	—	500	
	BC182	—	2.0	4.0	
BC183	—	2.0	10		
BC184	—	2.0	10		
BC184	—	2.0	4.0		

 1. Pulse Test: T_p 300 s, Duty Cycle 2.0%.

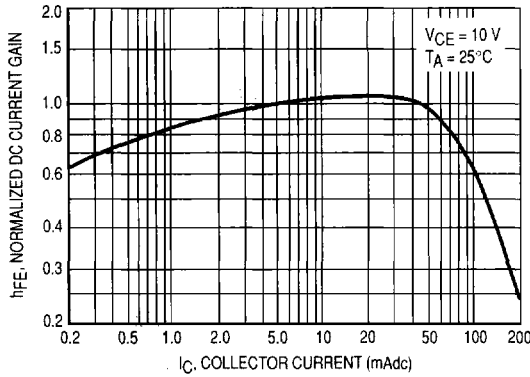


Figure 1. Normalized DC Current Gain

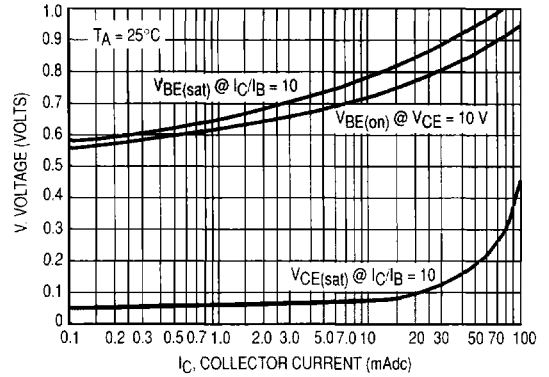


Figure 2. "Saturation" and "On" Voltages

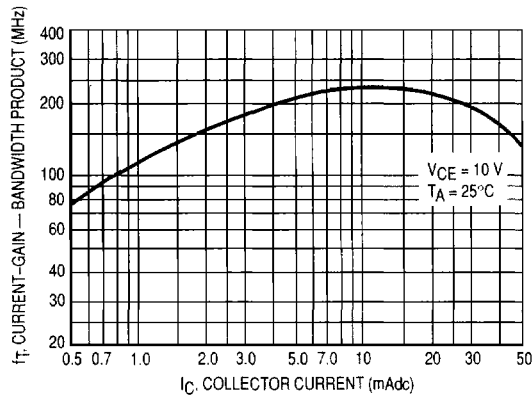


Figure 3. Current-Gain — Bandwidth Product

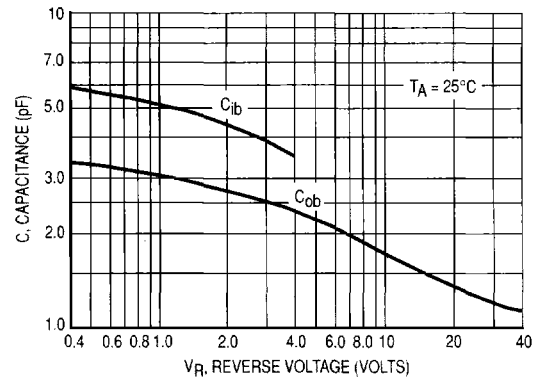


Figure 4. Capacitances

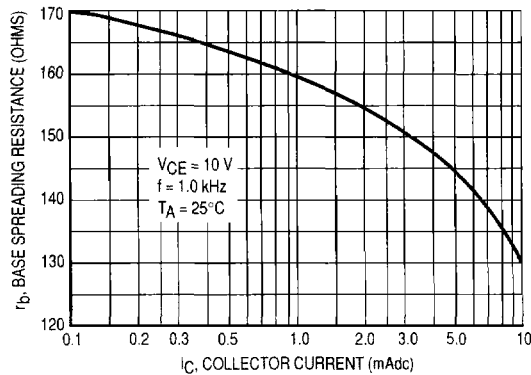


Figure 5. Base Spreading Resistance